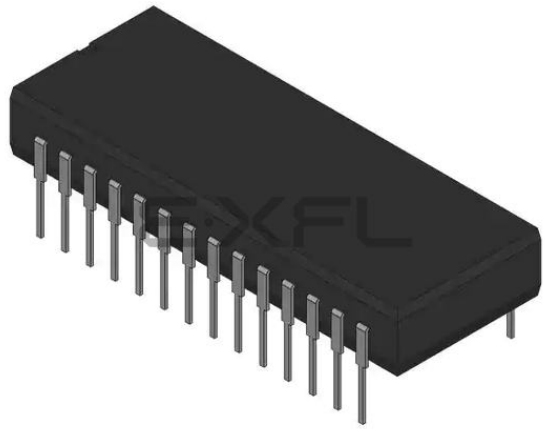

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Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	S08
Core Size	8-Bit
Speed	51.34MHz
Connectivity	I²C, LINbus, SCI, SPI
Peripherals	LVD, POR, PWM, WDT
Number of I/O	22
Program Memory Size	16KB (16K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	1K x 8
Voltage - Supply (Vcc/Vdd)	2.7V ~ 5.5V
Data Converters	A/D 13x12b; D/A 3x5b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	28-SOIC (0.295", 7.50mm Width)
Supplier Device Package	28-SOIC
Purchase URL	https://www.e-xfl.com/pro/item?MUrl=&PartUrl=mc9s08mp16vwl

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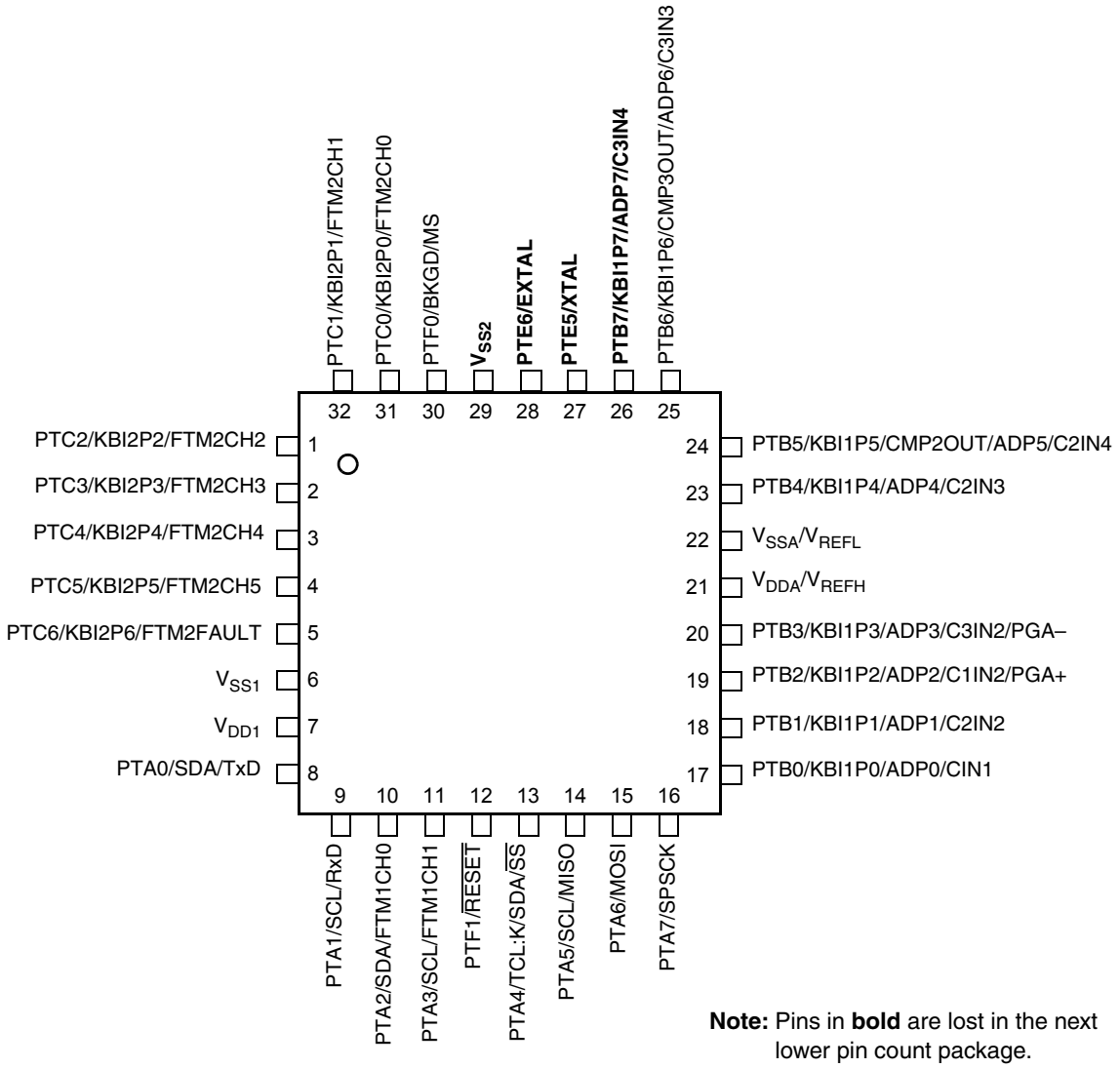


Note: Pins in **bold** are lost in the next lower pin count package.

Figure 3. MC9S08MP16 Series in 32-Pin LQFP Package

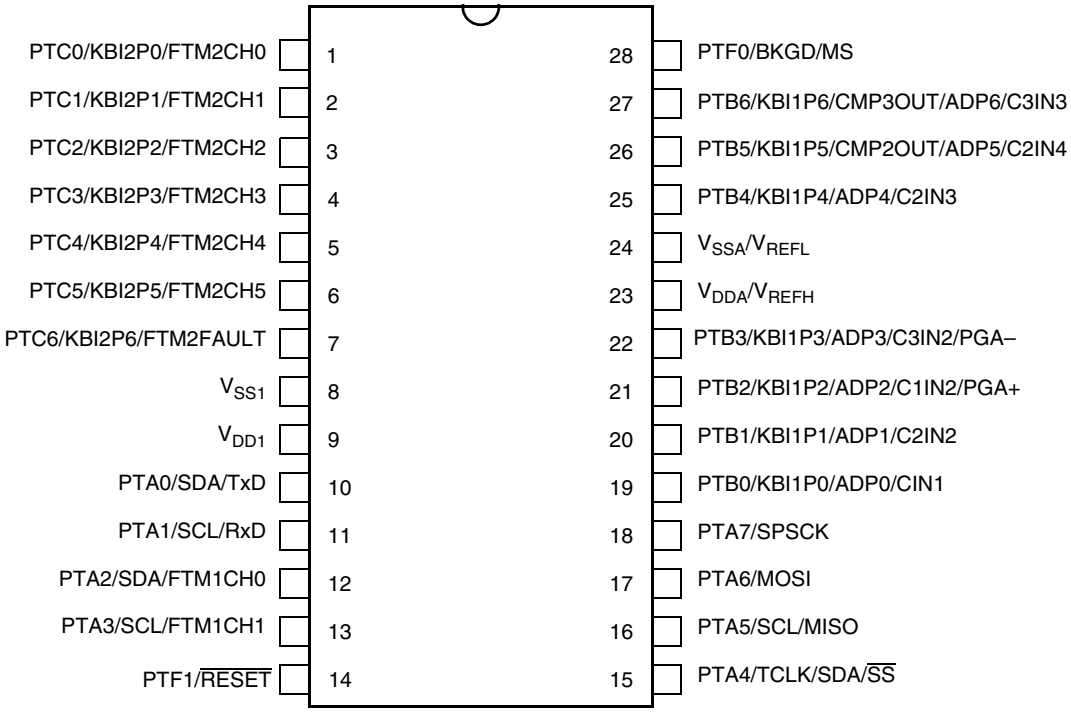


Figure 4. MC9S08MP16 Series in 28-Pin SOIC Package

Table 1. Pin Availability by Package Pin-Count

Pin Number			<-- Lowest Priority --> Highest				
48	32 LQFP	28	Port Pin	Alt 1	Alt 2	Alt3	Alt4
1	3	5	PTC4	KBI2P4	FTM2CH4		
2	4	6	PTC5	KBI2P5	FTM2CH5		
3	5	7	PTC6	KBI2P6	FTM2FAULT		
4	—	—	PTC7	KBI2P7	TCLK[1]		
5	—	—	PTD0	KBI3P0	SDA[5]		
6	—	—	PTD1	KBI3P1	SCL[5]		
7	—	—	PTD2	KBI3P2	PDB1OUT		
8	—	—	PTD3	KBI3P3	FTM1FAULT		
9	6	8					V_{SS1}
10	7	9					V_{DD1}
11	8	10	PTA0	SDA[5]	TxD		
12	9	11	PTA1	SCL[5]	RxD		
13	10	12	PTA2	SDA[5]	FTM1CH0		
14	11	13	PTA3	SCL[5]	FTM1CH1		
15	—	—	PTD4	KBI3P4	PDB2OUT		
16	—	—	PTD5	KBI3P5	CMP1OUT		
17	—	—	PTD6	KBI3P6	CMP2OUT[2]		
18	—	—	PTD7	KBI3P7	CMP3OUT[3]		
19	12	14	PTF1	$\overline{\text{RESET}}$[4]			
20	—	—	PTF2				
21	13	15	PTA4	TCLK[1]	SDA[5]	$\overline{SS}$	
22	14	16	PTA5		SCL[5]	MISO	
23	15	17	PTA6			MOSI	
24	16	18	PTA7			SPSCK	
25	—	—	PTE0		ADP8		
26	—	—	PTE1		ADP9		
27	—	—	PTE2		ADP10		
28	17	19	PTB0	KBI1P0	ADP0[6]	CIN1[6]	
29	18	20	PTB1	KBI1P1	ADP1[6]	C2IN2[6]	
30	19	21	PTB2	KBI1P2	ADP2[6]	C1IN2[6]	PGA+[6]
31	20	22	PTB3	KBI1P3	ADP3[6]	C3IN2[6]	PGA–[6]
32	21	23					V_{DDA}/V_{REFH}
33	22	24					V_{SSA}/V_{REFL}
34	—	—	PTE3		ADP11[6]	C1IN3[6]	

2.2 Parameter Classification

The electrical parameters shown in this supplement are guaranteed by various methods. To give the customer a better understanding the following classification is used and the parameters are tagged accordingly in the tables where appropriate:

Table 2. Parameter Classifications

P	Those parameters that are guaranteed during production testing on each individual device.
C	Those parameters that are achieved by the design characterization by measuring a statistically relevant sample size across process variations.
T	Those parameters that are achieved by design characterization on a small sample size from typical devices under typical conditions unless otherwise noted. All values shown in the typical column are within this category.
D	Those parameters that are derived mainly from simulations.

NOTE

The classification is shown in the column labeled “C” in the parameter tables where appropriate.

2.3 Absolute Maximum Ratings

Absolute maximum ratings are stress ratings only, and functional operation at the maxima is not guaranteed. Stress beyond the limits specified in Table 3 may affect device reliability or cause permanent damage to the device. For functional operating conditions, refer to the remaining tables in this section.

This device contains circuitry protecting against damage due to high static voltage or electrical fields; however, it is advised that normal precautions be taken to avoid application of any voltages higher than maximum-rated voltages to this high-impedance circuit. Reliability of operation is enhanced if unused inputs are tied to an appropriate logic voltage level (for instance, either V_{SS} or V_{DD}) or the programmable pull-up resistor associated with the pin is enabled.

Table 3. Absolute Maximum Ratings

Rating	Symbol	Value	Unit
Supply voltage	V_{DD}	–0.3 to +5.8	V
Maximum current into V_{DD}	I_{DD}	120	mA
Digital input voltage	V_{In}	–0.3 to V_{DD} + 0.3	V
Instantaneous maximum current Single pin limit (applies to all port pins)[1, 2, 3]	I_D	± 25	mA
Storage temperature range	T_{stg}	–55 to 150	°C

1 Input must be current limited to the value specified. To determine the value of the required current-limiting resistor, calculate resistance values for positive (V_{DD}) and negative (V_{SS}) clamp voltages, then use the larger of the two resistance values.

2 All functional non-supply pins, except for PTF1/$\overline{\text{RESET}}$ are internally clamped to V_{SS} and V_{DD}.

3 Power supply must maintain regulation within operating V_{DD} range during instantaneous and operating maximum current conditions. If positive injection current ($V_{In} > V_{DD}$) is greater than I_{DD}, the injection current may flow out of V_{DD} and could result in external power supply going out of regulation. Ensure external V_{DD} load will shunt current greater than maximum injection current. This will be the greatest risk when the MCU is not consuming power. Examples are: if no system clock is present, or if the clock rate is very low (which would reduce overall power consumption).

where K is a constant pertaining to the particular part. K can be determined from equation 3 by measuring P_D (at equilibrium) for a known T_A. Using this value of K, the values of P_D and T_J can be obtained by solving Equation 1 and Equation 2 iteratively for any value of T_A.

2.5 ESD Protection and Latch-Up Immunity

Although damage from electrostatic discharge (ESD) is much less common on these devices than on early CMOS circuits, normal handling precautions should be taken to avoid exposure to static discharge. Qualification tests are performed to ensure that these devices can withstand exposure to reasonable levels of static without suffering any permanent damage.

All ESD testing is in conformity with AEC-Q100 Stress Test Qualification for Automotive Grade Integrated Circuits. During the device qualification, ESD stresses were performed for the human body model (HBM) and the charge device model (CDM).

A device is defined as a failure if after exposure to ESD pulses the device no longer meets the device specification. Complete DC parametric and functional testing is performed per the applicable device specification at room temperature followed by hot temperature, unless instructed otherwise in the device specification.

Table 5. ESD and Latch-up Test Conditions

Model	Description	Symbol	Value	Unit
Human Body	Series resistance	R1	1500	Ω
	Storage capacitance	C	100	pF
	Number of pulses per pin	—	3	
Latch-up	Minimum input voltage limit		– 2.5	V
	Maximum input voltage limit		7.5	V

Table 6. ESD and Latch-Up Protection Characteristics

No.	Rating[1]	Symbol	Min	Max	Unit
1	Human body model (HBM)	V_{HBM}	± 2000	—	V
2	Charge device model (CDM)	V_{CDM}	± 500	—	V
3	Latch-up current at T_A = 125°C	I_{LAT}	± 100	—	mA

1 Parameter is achieved by design characterization on a small sample size from typical devices under typical conditions unless otherwise noted.

2.6 DC Characteristics

This section includes information about power supply requirements and I/O pin characteristics.

Table 7. DC Characteristics

Num	C	Characteristic	Symbol	Condition	Min	Typ[1]	Max	Unit
1	—	Operating Voltage	V_{DD}		2.7	—	5.5	V
2	—	Analog Supply voltage delta to V_{DD} (V_{DD} – V_{DDA})[(2)]	ΔV_{DDA}		—	0	±100	mV
3	—	Analog Ground voltage delta to V_{SS} (V_{SS} – V_{SSA})[(2)]	ΔV_{SSA}		—	0	±100	mV

Table 7. DC Characteristics (continued)

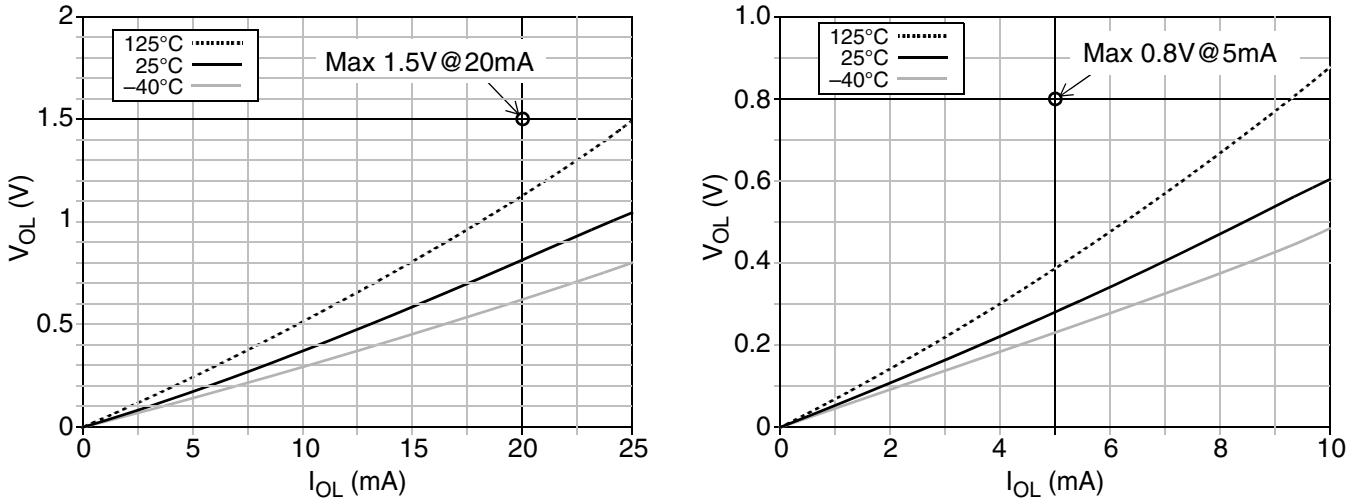
Num	C	Characteristic	Symbol	Condition	Min	Typ[1]	Max	Unit
4	C	All I/O pins (except PTF1/$\overline{\text{RESET}}$)	V_{OH}	5 V, I_{Load} = –4 mA	V_{DD} – 1.5	—	—	V
	P	low-drive strength		5 V, I_{Load} = –2 mA	V_{DD} – 0.8	—	—	
	C	Output high		3 V, I_{Load} = –1 mA	V_{DD} – 0.8	—	—	
	C	voltage		5 V, I_{Load} = –20 mA	V_{DD} – 1.5	—	—	
	P	high-drive strength		5 V, I_{Load} = –10 mA	V_{DD} – 0.8	—	—	
	C			3 V, I_{Load} = –5 mA	V_{DD} – 0.8	—	—	
5	D	Output high current — Max total I_{OH} for all ports	I_{OHT}	$V_{OUT} < V_{DD}$	0	—	–100	mA
6	C	All I/O pins	V_{OL}	5 V, I_{Load} = 4 mA	—	—	1.5	V
	P	(except PTF1/$\overline{\text{RESET}}$)		5 V, I_{Load} = 2 mA	—	—	0.8	
	C	low-drive strength		3 V, I_{Load} = 1 mA	—	—	0.8	
	C	All I/O pins		5 V, I_{Load} = 20 mA	—	—	1.5	
	P	Output low (Except PTF1/$\overline{\text{RESET}}$)		5 V, I_{Load} = 10 mA	—	—	0.8	
	C	voltage high-drive strength		3 V, I_{Load} = 5 mA	—	—	0.8	
7	C	PTF1/$\overline{\text{RESET}}$		5 V, I_{Load} = 3.2 mA	—	—	1.5	
8	P			5 V, I_{Load} = 1.6 mA	—	—	0.8	
9	C			3 V, I_{Load} = 0.8 mA	—	—	0.8	
10	D	Output low current — Max total I_{OL} for all ports	I_{OLT}	$V_{OUT} > V_{SS}$	0	—	100	mA
11	P	Input high voltage; all digital inputs	V_{IH}	5V	0.65 x V_{DD}	—	—	V
	C			3V	0.7 x V_{DD}	—	—	
12	P	Input low voltage; all digital inputs	V_{IL}	5V	—	—	0.35 x V_{DD}	V
	C			3V	—	—	0.35 x V_{DD}	
13	C	Input hysteresis	V_{hys}		0.06 x V_{DD}			V
14	P	Input leakage current (per pin)	$\lvert I_{In} \rvert$	$V_{In} = V_{DD}$ or V_{SS}	—	—	1	µA
15	P	Hi-Z (off-state) leakage current (per pin)						
		input/output port pins	$\lvert I_{OZ} \rvert$	$V_{In} = V_{DD}$ or V_{SS}	—	—	1	µA
		PTF1/$\overline{\text{RESET}}$, PTE5/XTAL pins		$V_{In} = V_{DD}$ or V_{SS}	—	—	2	µA
16	P	Pullup or Pulldown[3] resistors; when enabled — I/O pins	R_{PU},R_{PD}		17	37	52	kΩ
	C	PTF1/$\overline{\text{RESET}}$[4]	R_{PU}		17	37	52	kΩ
17	D	DC injection current [5, 6, 7, 8] — Single pin limit	I_{IC}	$V_{IN} > V_{DD}$	0	—	2	mA
				$V_{IN} < V_{SS}$	0	—	–0.2	mA
		Total MCU limit, includes sum of all stressed pins		$V_{IN} > V_{DD}$	0	—	25	mA
				$V_{IN} < V_{SS}$	0	—	–5	mA

7 All functional non-supply pins except PTF1/$\overline{\text{RESET}}$ are internally clamped to V_{SS} and V_{DD}.

8 The PTF1/$\overline{\text{RESET}}$ pin does not have a clamp diode to V_{DD}. Do not drive this pin above V_{DD}.

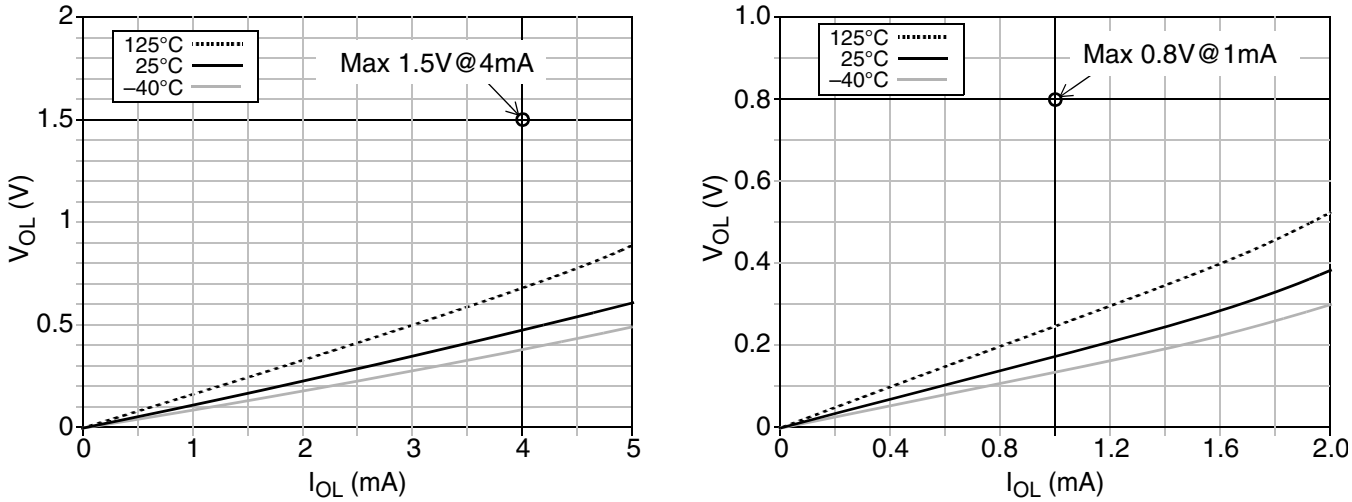
9 Maximum is highest voltage that POR is guaranteed.

10 Factory trimmed at V_{DD} = 5.0 V



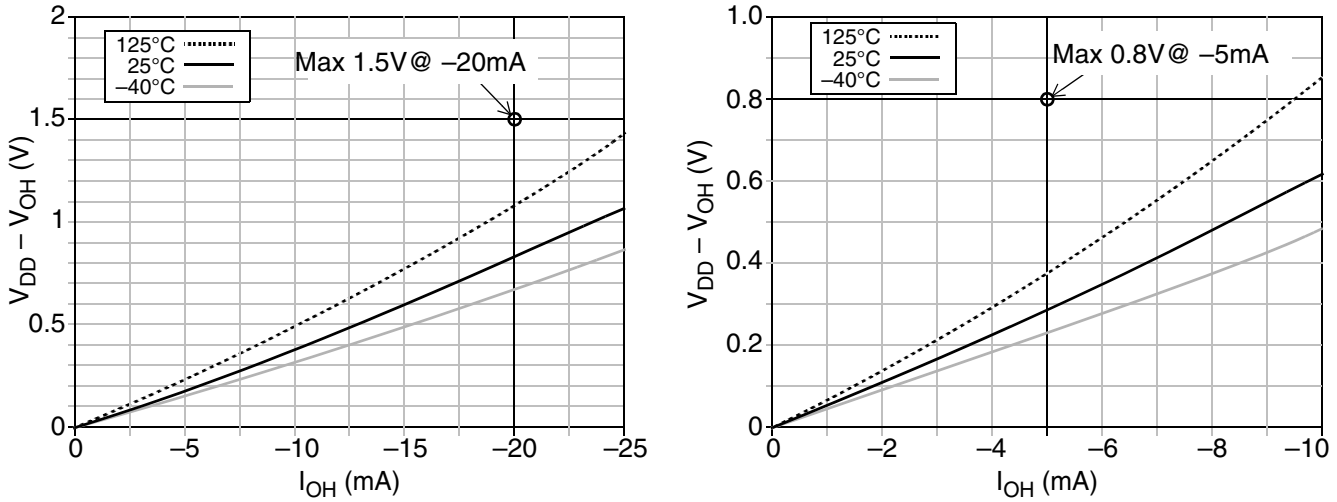
a) V_{DD} = 5V, High Drive **b) V_{DD} = 3V, High Drive**

Figure 5. Typical V_{OL} vs I_{OL}, High Drive Strength (except PTF1/RESET)



a) V_{DD} = 5V, Low Drive **b) V_{DD} = 3V, Low Drive**

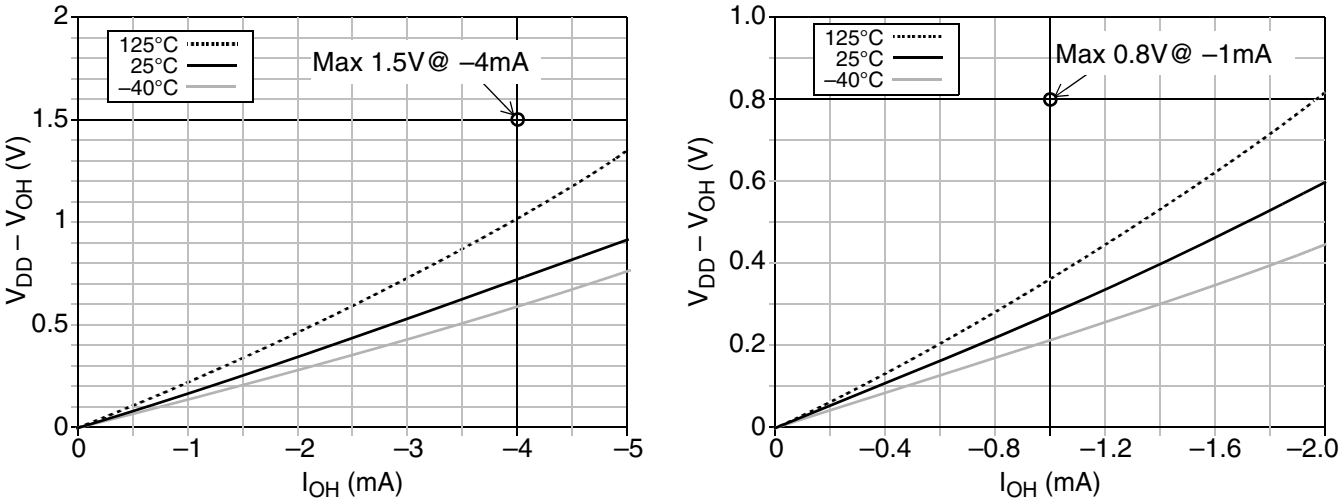
Figure 6. Typical V_{OL} vs I_{OL}, Low Drive Strength (except PTF1/RESET)



a) V_{DD} = 5V, High Drive

b) V_{DD} = 3V, High Drive

Figure 7. Typical $V_{DD} – V_{OH}$ vs I_{OH}, High Drive Strength



a) V_{DD} = 5V, Low Drive

b) V_{DD} = 3V, Low Drive

Figure 8. Typical $V_{DD} – V_{OH}$ vs I_{OH}, Low Drive Strength

2.7 Supply Current Characteristics

This section includes information about power supply current in various operating modes.

Table 8. Supply Current Characteristics

Num	C	Parameter	Symbol	V_{DD} (V)	Typ[1]	Max[2]	Unit
1	C	Run supply current[3] measured at (CPU clock = 4 MHz, f_{Bus} = 2 MHz)	RI_{DD}	5	2.16	3	mA
	C			3	1.8	2.5	
2	P	Run supply current[3] measured at (CPU clock = 16 MHz, f_{Bus} = 8 MHz)	RI_{DD}	5	5.26	7.5	mA
	C			3	4.92	7	

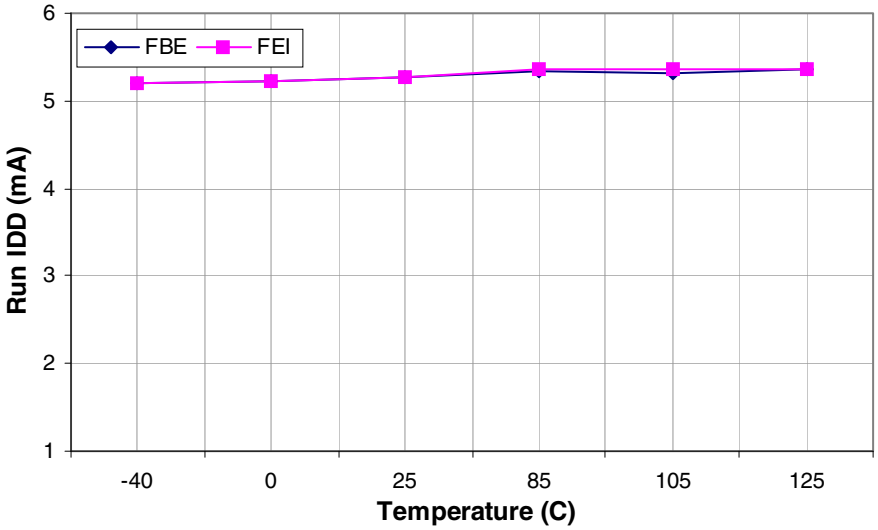


Figure 10. Typical Run I_{DD} vs. Temperature (V_{DD} = 5V, f_{bus} = 8MHz)

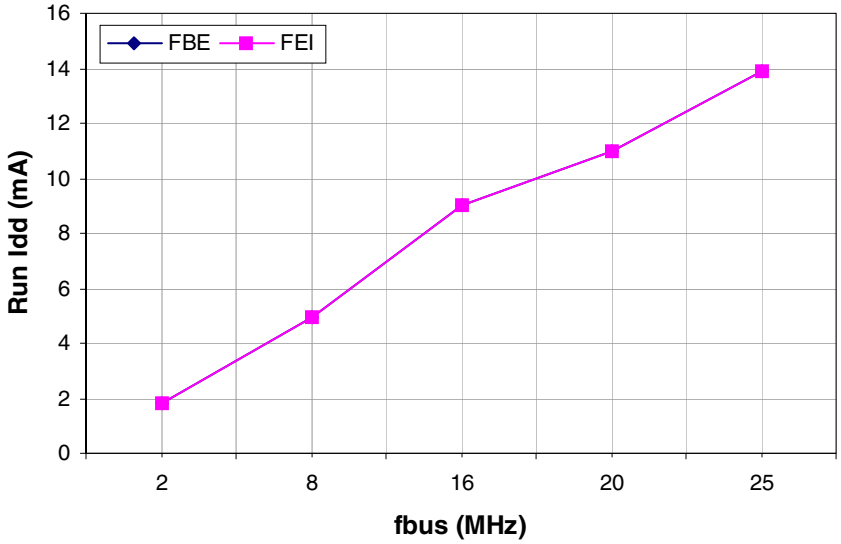


Figure 11. Typical Run I_{DD} vs. Bus Frequency (V_{DD} = 3V)

Table 9. Oscillator Electrical Specifications (continued)

Num	C	Rating	Symbol	Min	Typ[1]	Max	Unit
5	T	Crystal start-up time [4] Low range, low gain (RANGE = 0, HGO = 0) Low range, high gain (RANGE = 0, HGO = 1) High range, low gain (RANGE = 1, HGO = 0)[5] High range, high gain (RANGE = 1, HGO = 1)[4]	 $t_{CSTL-LP}$ $t_{CSTL-HGO}$ $t_{CSTH-LP}$ $t_{CSTH-HGO}$	 — — — —	 200 400 5 20	 — — — —	ms
6	T	Square wave input clock frequency (EREFS = 0, ERCLKEN = 1) FEE mode [2] FBE mode [3] FBELP mode	f_{extal}	 0.03125 0 0	 — — —	 51.34 51.34 51.34	 MHz MHz MHz

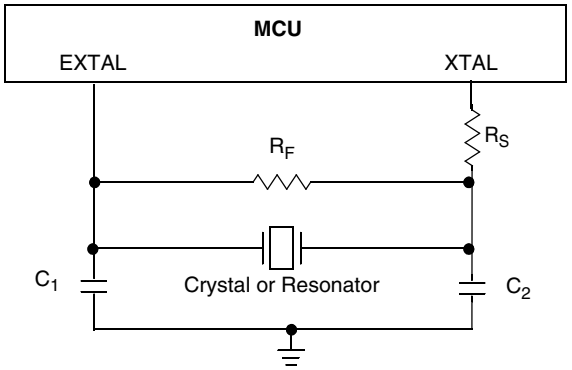
1 Typical data was characterized at 5.0 V, 25°C or is recommended value.

2 The input clock source must be divided using RDIV to within the range of 31.25 kHz to 39.0625 kHz.

3 The input clock source must be divided using RDIV to less than or equal to 39.0625 kHz.

4 This parameter is characterized and not tested on each device. Proper PC board layout procedures must be followed to achieve specifications.

5 4 MHz crystal



2.9 Internal Clock Source (ICS) Characteristics

Table 10. ICS Frequency Specifications

Num	C	Characteristic	Symbol	Min	Typ[1]	Max	Unit
1a	P	Average internal reference frequency — factory trimmed (consumer- and industrial-qualified devices) at V_{DD} = 5 V and temperature = 25°C	f_{int_t}	—	32.768	—	kHz
1b	P	Average internal reference frequency — factory trimmed (automotive-qualified devices) at V_{DD} = 5 V and temperature = 25°C	f_{int_t}	—	31.25	—	kHz
2	P	Internal reference frequency — user trimmed	f_{int_t}	31.25	—	39.06	kHz
3	T	Internal reference start-up time	t_{irefst}	—	60	100	µs

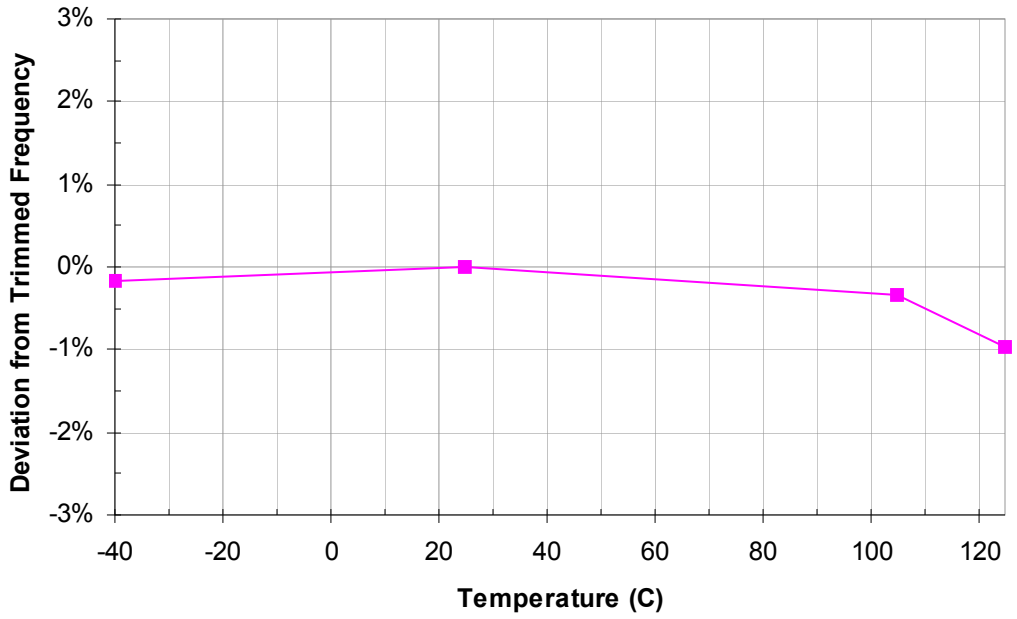


Figure 15. Typical Frequency Deviation vs Temperature (ICS Trimmed to 25 MHz bus@25°C, 5V, FEI)[1]

2.10 ADC Characteristics

Table 11. 12-bit ADC Operating Conditions

Characteristic	Conditions	Symbol	Min	Typ[1]	Max	Unit	Comment
Supply voltage	Absolute	V_{DDA}	2.7	—	5.5	V	
Input Voltage		V_{ADIN}	V_{REFL}	—	V_{REFH}	V	
Input Capacitance		C_{ADIN}	—	4.5	5.5	pF	
Input Resistance		R_{ADIN}	—	3	5	kΩ	
Analog Source Resistance	12 bit mode f_{ADCK} > 4MHz f_{ADCK} < 4MHz	R_{AS}	 — —	 — —	 2 5	kΩ	External to MCU
	10 bit mode f_{ADCK} > 4MHz f_{ADCK} < 4MHz		 — —	 — —	 5 10		
	8 bit mode (all valid f_{ADCK})		—	—	10		
ADC Conversion Clock Freq.	High Speed (ADLPC=0)	f_{ADCK}	0.4	—	8.0	MHz	
	Low Power (ADLPC=1)		0.4	—	4.0		

[1] Typical values assume V_{DDAD} = 5.0V, Temp = 25°C, f_{ADCK}=1.0MHz unless otherwise stated. Typical values are for reference only and are not tested in production.

1. Based on the average of several hundred units from a typical characterization lot.

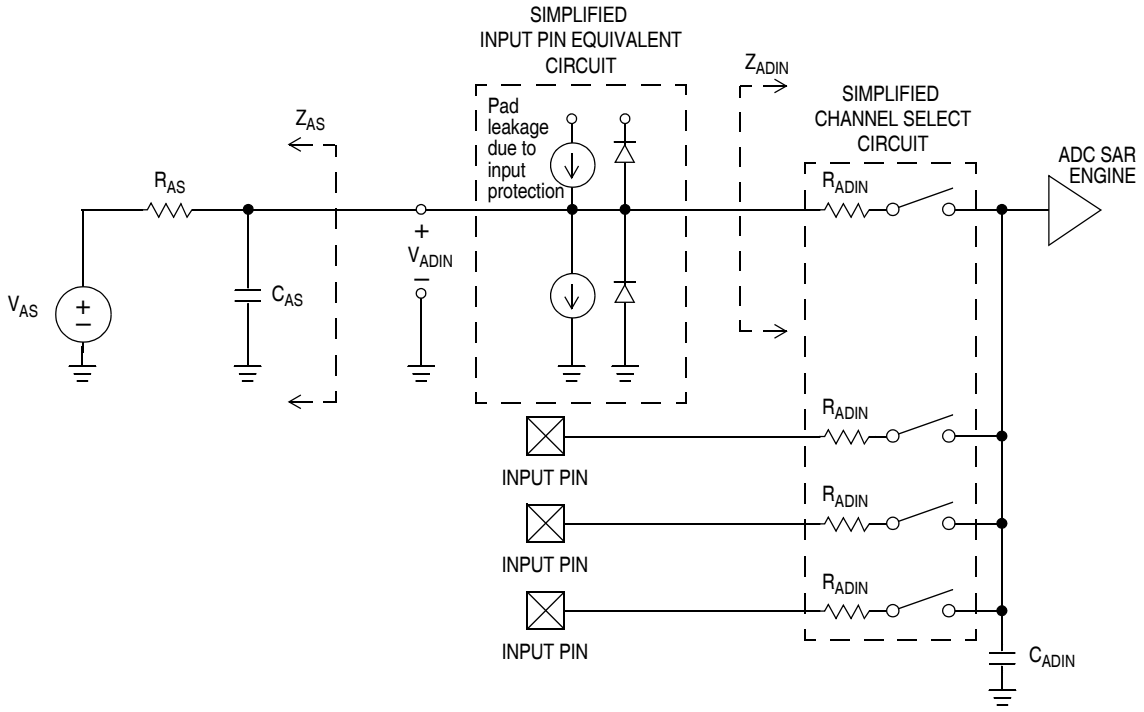


Figure 16. ADC Input Impedance Equivalency Diagram

Table 12. 12-bit ADC Characteristics (V_{REFH} = V_{DDAD}, V_{REFL} = V_{SSAD})

C	Characteristic	Conditions	Symb	Min	Typ[1]	Max	Unit	Comment
T	Supply Current ADLPC=1 ADLSMP=1 ADCO=1		I_{DDA}	—	133	—	μA	
T	Supply Current ADLPC=1 ADLSMP=0 ADCO=1		I_{DDA}	—	218	—	μA	
T	Supply Current ADLPC=0 ADLSMP=1 ADCO=1		I_{DDA}	—	327	—	μA	
T	Supply Current ADLPC=0 ADLSMP=0 ADCO=1		I_{DDA}	—	0.582	—	mA	
P	ADC Asynchronous Clock Source	High Speed (ADLPC=0)	f_{ADACK}	2	3.3	5	MHz	t_{ADACK} = $1/f_{ADACK}$
		Low Power (ADLPC=1)		1.25	2	3.3		

Table 15. Programmable Gain Amplifier Electrical Specifications (continued)

Num	C	Parameter	Symbol	Min	Typical	Max	Unit
4	D	Differential input voltage	$V_{DIFFMAX}$	$-\left(\frac{V_{DDA}-1.4}{2\times Gain}\right)$	0	$\frac{V_{DDA}-1.4}{2\times Gain}$	V
5	T	Linearity (@ voltage gain)[1] • 1x • 2x • 4x • 8x • 16x • 32x	L_V	 1 – 1/2 LSB 2 – 1/2 LSB 4 – 1 LSB 8 – 1 LSB 16 – 4 LSB 32 – 4 LSB	 1 2 4 8 16 32	 1 + 1/2 LSB 2 + 1/2 LSB 4 + 1 LSB 8 + 1 LSB 16 + 4 LSB 32 + 4 LSB	V/V
6	T	Max gain error	E_G	—	1	2	%
7a	D	PGA clock • normal mode (LP=0) • low power mode (LP=1)	f_{PGA}	 — —	 8[2] 4	 8[2] 4	MHz
7b	D	PGA sampling frequency[3]	f_{SAMPL}	—	$\frac{1}{\left(\frac{12+18\times NUM\_CLK\_GS}{f_{PGA}}\right)+\frac{43}{f_{ADC}}+\frac{5}{f_{BUS}}}$	—	Samples per second
8	D	Input signal bandwidth	BW	0	$f_{SAMPL} \div 8$	$f_{SAMPL} \div 2$	Hz
9	D	Charge pump clock frequency	f_{cpclk}	100	$f_{PGA} \div 4$	—	Hz

1 LSB in 12-bit resolution

2 8 MHz is required for PGA achieving 1 µs sampling time.

3 ADC in 12-bit mode, long sampling time, $f_{ADC} = f_{PGA}$

2.14 AC Characteristics

This section describes timing characteristics for each peripheral system.

2.14.1 Control Timing

Table 16. Control Timing

Num	C	Rating		Symbol	Min	Typ[1]	Max	Unit
1	D	Bus frequency ($t_{cyc} = 1/f_{Bus}$)	–40 to 105 °C	f_{Bus}	DC	—	25.67	MHz
			–40 to 125 °C	f_{Bus}	DC	—	20	MHz
2	P	Internal low power oscillator period		t_{LPO}	700	—	1300	µs
3	D	External reset pulse width[2]		t_{extrst}	100	—	—	ns
4	D	Reset low drive		t_{rstdrv}	34 x t_{cyc}	—	—	ns
5	D	BKGD/MS setup time after issuing background debug force reset to enter user or BDM modes		t_{MSSU}	500	—	—	ns
6	D	BKGD/MS hold time after issuing background debug force reset to enter user or BDM modes [3]		t_{MSH}	100	—	—	µs

Table 16. Control Timing (continued)

Num	C	Rating	Symbol	Min	Typ[1]	Max	Unit
7	D	Keyboard interrupt pulse width Asynchronous path[4] Synchronous path[5]	t_{ILIH}, t_{IHIL}	 100 1.5 x t_{cyc}	 — —	 — —	ns
8	C	Port rise and fall time — Low output drive (PTxDS = 0) (load = 50 pF)[6] Slew rate control disabled (PTxSE = 0) Slew rate control enabled (PTxSE = 1)	t_{Rise}, t_{Fall}	 — —	 40 75	 — —	ns
		Port rise and fall time — High output drive (PTxDS = 1) (load = 50 pF)[6] Slew rate control disabled (PTxSE = 0) Slew rate control enabled (PTxSE = 1)	t_{Rise}, t_{Fall}	 — —	 11 35	 — —	ns

1 Typical values are based on characterization data at V_{DD} = 5.0V, 25°C unless otherwise stated.

2 This is the shortest pulse that is guaranteed to be recognized as a reset pin request.

3 To enter BDM mode following a POR, BKGD/MS should be held low during the power-up and for a hold time of t_{MSH} after V_{DD} rises above V_{LVD}.

4 This is the minimum pulse width that is guaranteed to be recognized as a keyboard interrupt request in stop mode.

5 This is the minimum pulse width that is guaranteed to pass through the pin synchronization circuitry. Shorter pulses may or may not be recognized. In stop mode, the synchronizer is bypassed so shorter pulses can be recognized in that case.

6 Timing is shown with respect to 20% V_{DD} and 80% V_{DD} levels. Temperature range –40°C to 125°C.

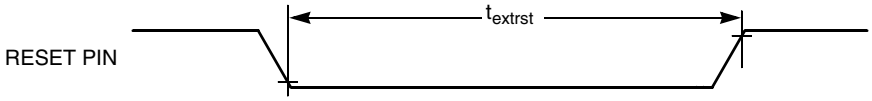


Figure 17. Reset Timing

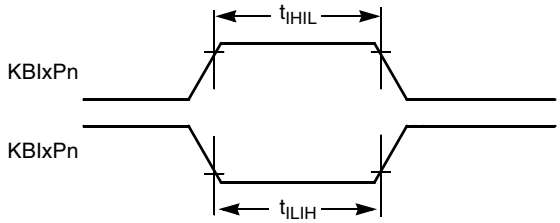


Figure 18. KBIxPn Timing

2.14.2 FTM Module Timing

Synchronizer circuits determine the shortest input pulses that can be recognized or the fastest clock that can be used as the optional external source to the FTM timer counter. These synchronizers operate from the current ICSOUT clock. The ICSOUT clock period = 0.5 × t_{cyc} = 1/(f_{Bus} × 2).

Table 17. FTM Input Timing

No.	C	Function	Symbol	Min	Max	Unit
1	D	External clock frequency	f_{TCLK}	0	f_{ICSOUT}/4[1]	Hz
2	D	External clock period	t_{TCLK}	2	—	t_{cyc}
3	D	External clock high time	t_{clkh}	0.75	—	t_{cyc}

Table 17. FTM Input Timing (continued)

No.	C	Function	Symbol	Min	Max	Unit
4	D	External clock low time	t_{clkl}	0.75	—	t_{cyc}
5	D	Input capture pulse width	t_{ICPW}	0.75	—	t_{cyc}

1 The maximum external clock frequency is limited to 10MHz due to input filter characteristics.

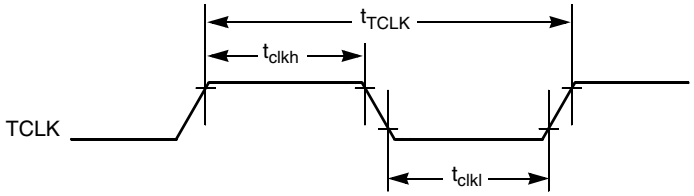


Figure 19. FTM External Clock

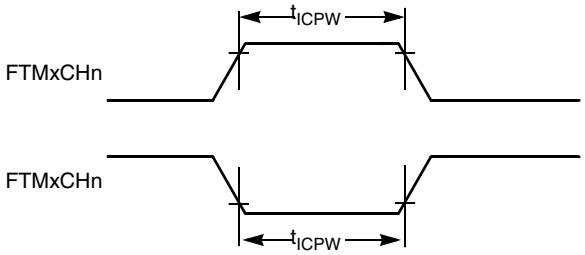


Figure 20. FTM Input Capture Pulse

2.14.3 MTIM Module Timing

Synchronizer circuits determine the fastest clock that can be used as the optional external clock source to the MTIM timer counter. These synchronizers operate from the current bus rate clock.

Table 18. MTIM Input Timing

No.	C	Function	Symbol	Min	Max	Unit
1	D	External clock frequency	f_{TCLK}	0	$f_{Bus}/4$	Hz
2	D	External clock period	t_{TCLK}	4	—	t_{cyc}
3	D	External clock high time	t_{clkh}	1.5	—	t_{cyc}
4	D	External clock low time	t_{clkl}	1.5	—	t_{cyc}

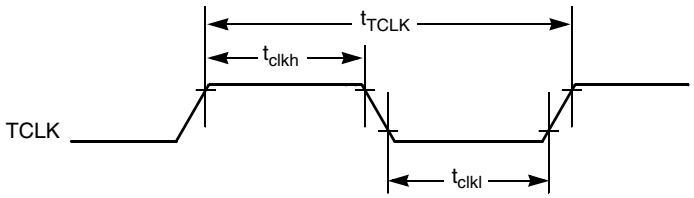
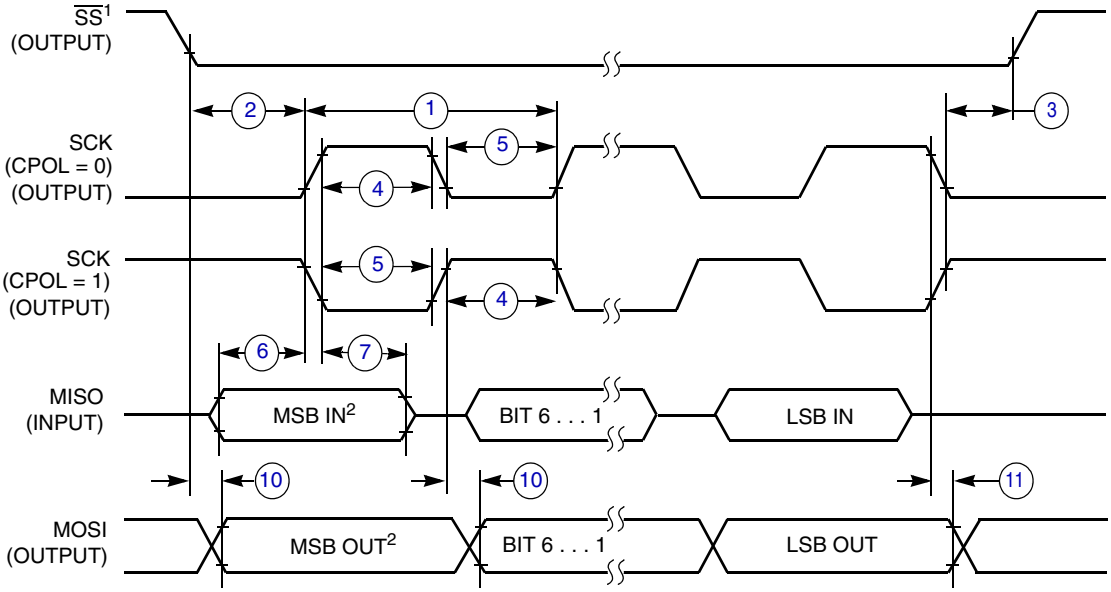
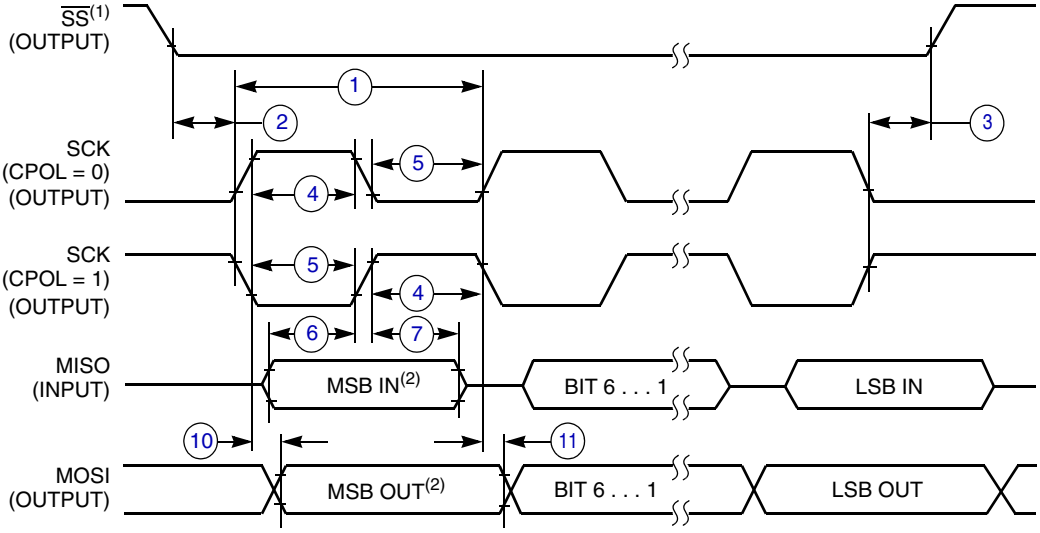


Figure 21. MTIM Timer External Clock



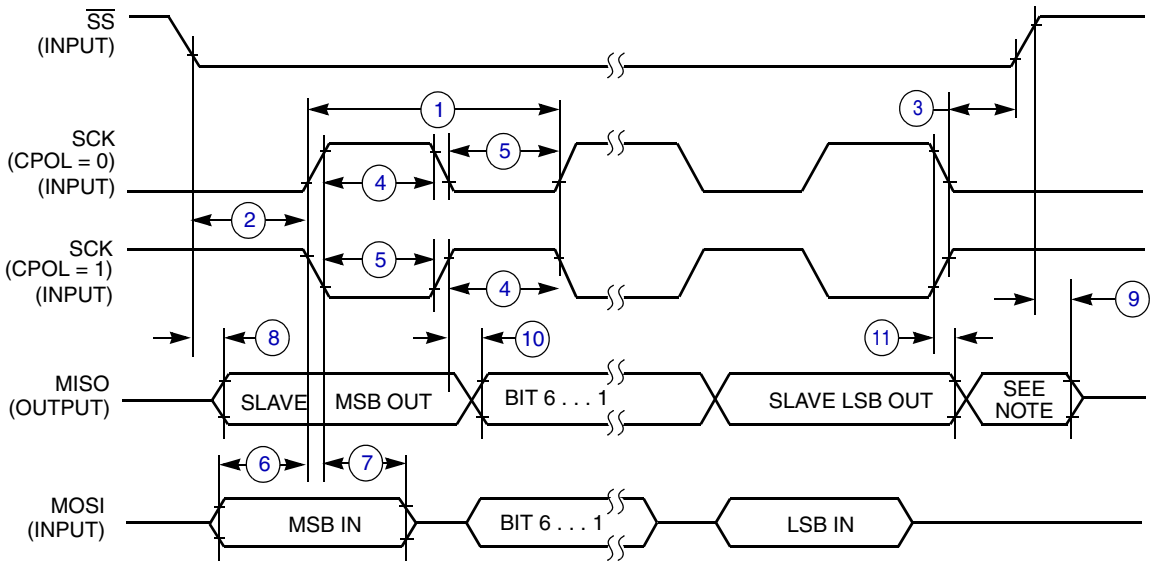
NOTES:
1. $\overline{SS}$ output mode (MODFEN = 1, SSOE = 1).
2. LSBF = 0. For LSBF = 1, bit order is LSB, bit 1, ..., bit 6, MSB.

Figure 22. SPI Master Timing (CPHA = 0)



NOTES:
1. $\overline{SS}$ output mode (MODFEN = 1, SSOE = 1).
2. LSBF = 0. For LSBF = 1, bit order is LSB, bit 1, ..., bit 6, MSB.

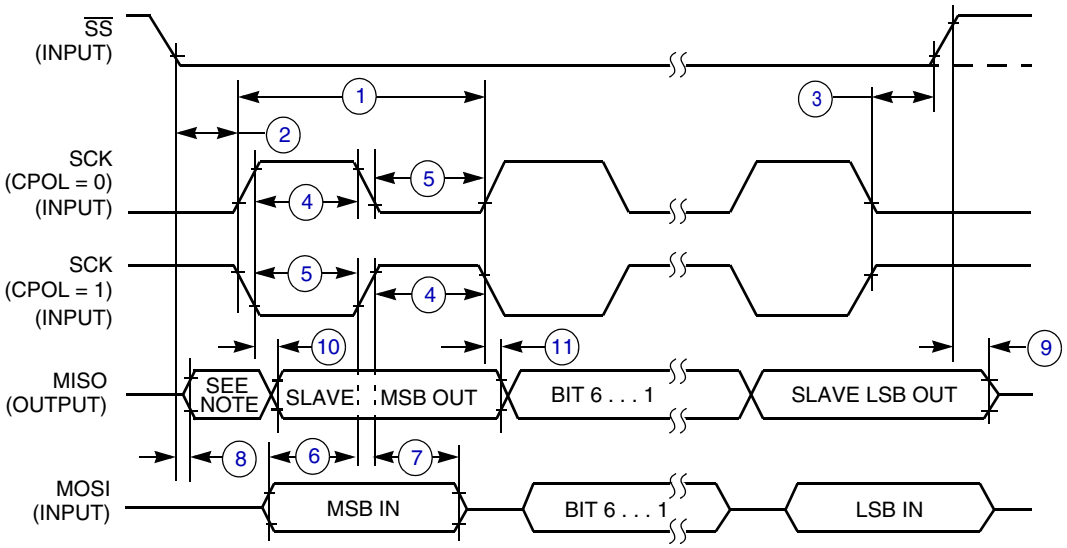
Figure 23. SPI Master Timing (CPHA = 1)



NOTE:

1. Not defined but normally MSB of character just received

Figure 24. SPI Slave Timing (CPHA = 0)



NOTE:

1. Not defined but normally LSB of character just received

Figure 25. SPI Slave Timing (CPHA = 1)

2.15 Flash Memory Specifications

This section provides details about program/erase times and program-erase endurance for the flash memory.

Program and erase operations do not require any special power sources other than the normal V_{DD} supply. For more detailed information about program/erase operations, see the Memory section.

Table 20. Flash Memory Characteristics

Num	C	Characteristic	Symbol	Min	Typical	Max	Unit
1	—	Supply voltage for program/erase -40°C to 125°C	$V_{prog/erase}$	2.7		5.5	V
2	—	Supply voltage for read operation	V_{Read}	2.7		5.5	V
3	—	Internal FCLK frequency[1]	f_{FCLK}	150		200	kHz
4	—	Internal FCLK period (1/FCLK)	t_{Fcyc}	5		6.67	µs
5	C	Byte program time (random location)[2]	t_{prog}	9			t_{Fcyc}
6	—	Byte program time (burst mode)[2]	t_{Burst}	4			t_{Fcyc}
7	D	Page erase time[2]	t_{Page}	4000			t_{Fcyc}
8	D	Mass erase time[2]	t_{Mass}	20,000			t_{Fcyc}
9	C	Byte program current[3]	R_{IDDBP}	—	4	—	mA
10	C	Page erase current[3]	R_{IDDPE}	—	6	—	mA
11	C	Program/erase endurance[4] T_L to T_H = –40°C to + 125°C T = 25°C		10,000	— 100,000	— —	cycles
12	C	Data retention[5]	t_{D_ret}	15	100	—	years

1 The frequency of this clock is controlled by a software setting.

2 These values are hardware state machine controlled. User code does not need to count cycles. This information supplied for calculating approximate time to program and erase.

3 The program and erase currents are additional to the standard run I_{DD}. These values are measured at room temperatures with V_{DD} = 5.0 V, bus frequency = 4.0 MHz.

4 **Typical endurance for Flash** is based upon the intrinsic bit cell performance. For additional information on how Freescale defines typical endurance, please refer to Engineering Bulletin EB619/D, *Typical Endurance for Nonvolatile Memory.*

5 **Typical data retention** values are based on intrinsic capability of the technology measured at high temperature and de-rated to 25°C using the Arrhenius equation. For additional information on how Freescale defines typical data retention, please refer to Engineering Bulletin EB618/D, *Typical Data Retention for Nonvolatile Memory.*

2.16 EMC Performance

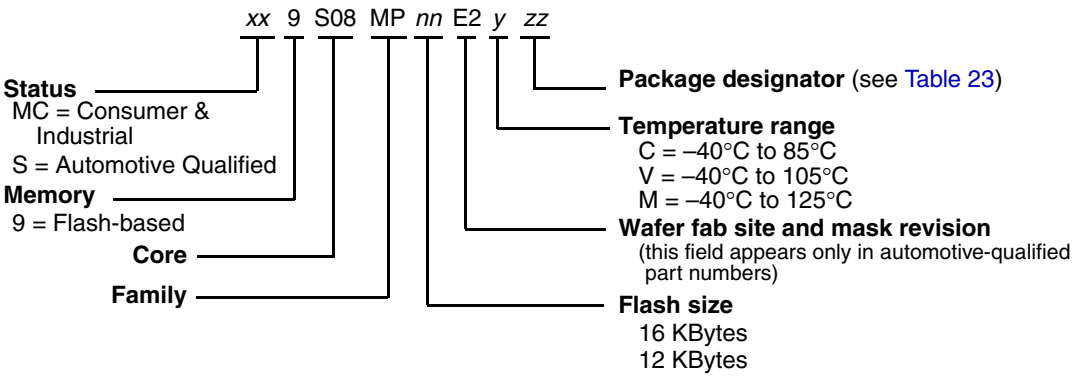
Electromagnetic compatibility (EMC) performance is highly dependant on the environment in which the MCU resides. Board design and layout, circuit topology choices, location and characteristics of external components as well as MCU software operation all play a significant role in EMC performance. The system designer should consult Freescale applications notes such as AN2321, AN1050, AN1263, AN2764, and AN1259 for advice and guidance specifically targeted at optimizing EMC performance.

2.16.1 Radiated Emissions

Microcontroller radiated RF emissions are measured from 150 kHz to 1 GHz using the TEM/GTEM Cell method in accordance with the IEC 61967-2 and SAE J1752/3 standards. The measurement is performed with the microcontroller installed on a

3.1 Device Numbering Scheme

Example of the device numbering system:



4 Package Information

The latest package outline drawings are available on the product summary pages on our web site: http://www.freescale.com/8bit. The following table lists the document numbers per package. Use these numbers in the web page's keyword search engine to find the latest package outline drawings.

NOTE

The 32 LQFP and 28 SOIC are not qualified to meet automotive requirements.

Table 23. Package Descriptions

Pin Count	Package Type	Abbreviation	Designator	Case No.	Document No.
48	Low Quad Flat Pack	LQFP	LF	932-03	98ASH00962A
32	Low Quad Flat Pack	LQFP	LC	873A-03	98ASH70029A
28	Small Outline Integrated Circuit	SOIC	WL	751F-05	98ASB42345B

5 Related Documentation

Find the most current versions of all documents at http://www.freescale.com.

Reference Manual (MC9S08MP16RM)

Contains extensive product information including modes of operation, memory, resets and interrupts, register definition, port pins, CPU, and all module information.

6 Revision History

To provide the most up-to-date information, the revision of our documents on the World Wide Web are the most current. Your printed copy may be an earlier revision. To verify you have the latest information available, refer to:

http://www.freescale.com